

IN THE CLAIMS:

Amend claims 5 and 6 to read:

5. (Amended) The row decoder according to Claim 3, wherein
in the erase mode, the select voltage is a positive voltage, while the non-select voltage is
a negative voltage; and

an absolute value the select voltage is equal to an absolute value of the negative voltage
applied to (the substrate or well) of the nonvolatile semiconductor storage device.

6. (Amended) The row decoder according to Claim 4, wherein
in the erase mode, the select voltage is a positive voltage, while the non-select voltage is
a negative voltage; and

an absolute value the select voltage is equal to an absolute value of the negative voltage
applied to (the substrate or well) of the nonvolatile semiconductor storage device.